

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	281	438/140,203,259,286,335.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 11:35
L2	236	257/335,339,340,409.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 11:35
S5	1	@pn="5640034"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 16:03
S6	0	@ad<"20000728" and source same trench same (high adj density adj diffusion) same electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:45
S27	7083	high adj voltage adj (device transistor DMOS MOSFET FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:44
S28	95	S27 and n near2 drift and p near2 drift	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:44
S29	86	S28 and gate and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:44
S30	24	S29 and trench same polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:44

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S31	4	S30 and second adj trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:44
S32	0	S31 and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 15:14
S33	472	S27 and trench same polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:45
S34	137	S33 and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:45
S35	27	S34 and second near2 trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:46
S36	7	S34 and second near2 trench same polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 14:46
S37	1	S30 and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 16:03
S38	175	conventional adj DMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 16:06

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S39	79	S38 and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 16:07
S40	90	conventional adj double adj diffused	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 16:06
S41	60	conventional adj double adj diffused near3 (MOS (metal adj oxide adj semiconductor) MOSFET FET transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 16:07
S42	29	S41 and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/29 16:07